Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor device comprising:

a first semiconductor chip with elements formed over a <u>first</u> semiconductor substrate;

a second semiconductor chip with elements formed over a <u>second</u> semiconductor substrate;

a wiring substrate including a main surface and a back surface on the side opposite to the main surface,

the second semiconductor chip <u>being</u> mounted over the main surface of the wiring substrate, <u>and</u>

the first semiconductor chip <u>being</u> stacked over the second semiconductor chip; and

an electrode of a fixed potential disposed over <u>a surface of</u> the first semiconductor chip on the side opposed to thereof which faces the second semiconductor chip,

wherein the electrode of the <u>a</u> fixed potential is electrically connected to the semiconductor substrate of the first semiconductor chip and to the wiring substrate.

2. (previously presented) A semiconductor device according to claim 1, wherein the second semiconductor chip is flip-connected to the wiring substrate.

- 3. (currently amended) A semiconductor device according to claim 2, wherein the another electrode of the a fixed potential is disposed over a surface of the second semiconductor chip on the side thereof which faces opposite to the first semiconductor chip.
- 4. (currently amended) A semiconductor device according to claim 3, wherein the other electrode of the a fixed potential and the wiring substrate are connected with each other through an electrically conductive wire.
- 5. (currently amended) A semiconductor device according to claim [[4]] 3, wherein the second semiconductor chip includes a projecting portion projecting beyond an edge of from the first semiconductor chip in a direction parallel to the main surface of the wiring substrate, the other electrode of the a fixed potential is disposed ever on the projecting portion of the second semiconductor chip, and the electrode of the a fixed potential disposed on ever the projecting portion and the wiring substrate are connected with each other through the an electrically conductive wire.
- 6. (currenţly amended) A semiconductor device according to claim 3, wherein a gold plating film is formed over a surface of the electrode of the a fixed potential.
- 7. (previously presented) A semiconductor device according to claim 4, wherein the electrically conductive wire is a gold wire.
- 8. (currently amended) A semiconductor device according to claim 1, further comprising:

an amplifier circuit for amplifying an input signal in threes-three stages, of which first-stage and second-stage amplifier circuits are incorporated in the first semiconductor chip and a third-stage amplifier circuit is incorporated in the second semiconductor chip.

9. (currently amended) A semiconductor device according to claim 1, wherein the ratio in projected area of each of main surfaces of the first and second semiconductor chips <u>relative</u> to the main surface of the wiring substrate is in the range of 0.9 to 1.1.

10. (currently amended) A semiconductor device comprising:

a first semiconductor chip with elements formed over a <u>first</u> semiconductor substrate;

<u>a</u> second semiconductor chip with elements formed over a <u>second</u> semiconductor substrate;

a wiring substrate including a main surface and a back surface on the side opposite to the main surface,

the second conductor <u>semiconductor</u> chip <u>being</u> mounted face up over the main surface of the wiring substrate, <u>and</u>

the first semiconductor chip <u>being</u> stacked over the second semiconductor chip; and

an electrode of a fixed potential disposed over <u>a surface of</u> the first semiconductor chip on the side opposed to the second semiconductor chip,

wherein the electrode of the <u>a</u> fixed potential is electrically connected to the semiconductor substrate of the first semiconductor chip and to the wiring substrate.

- 11. (previously presented) A semiconductor device according to claim 10, wherein the second semiconductor chip and the wiring substrate are connected with each other through an electrically conductive wire.
- 12. (previously presented) A semiconductor device according to claim 10, wherein a spacer is disposed between the first and second semiconductor chips.
- 13. (currently amended) A semiconductor device according to claim 12, wherein the electrode of the <u>a</u> fixed potential is disposed over the spacer on the side thereof opposed to the first semiconductor chip.